



# SUR522H

Epitaxial Planar Type NPN Silicon Transistor

## Description

- Digital transistor

## Features

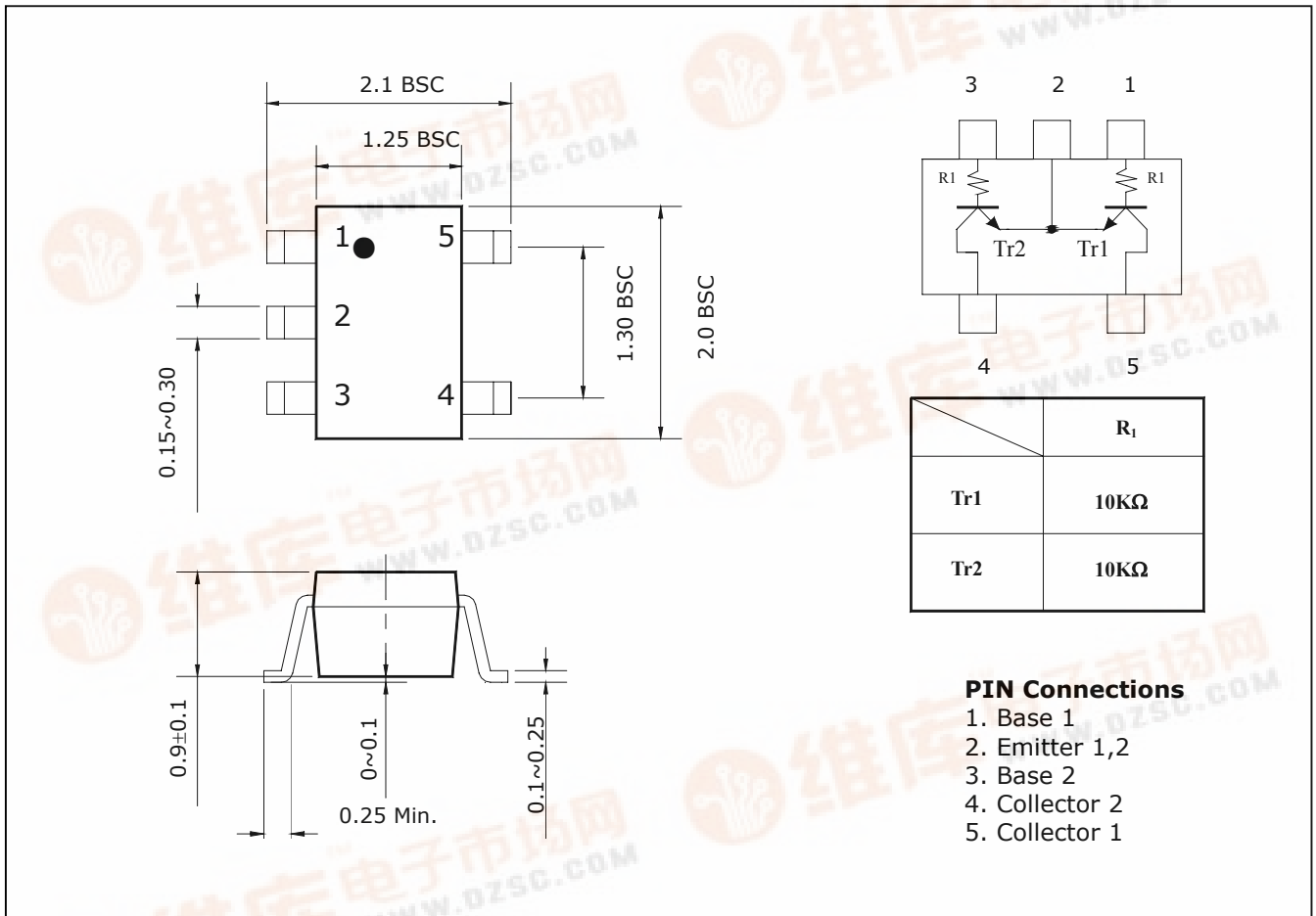
- Two SRC1211 chips in SOT-353 package
- With built-in bias resistors

## Ordering Information

Type NO.	Marking	Package Code
SUR522H	22H	SOT-353

## Outline Dimensions

unit : mm



# SUR522H

## Absolute maximum ratings [Tr1, Tr2 : NPN ]

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Out Voltage	V <sub>O</sub>	50	V
Input Voltage	V <sub>I</sub>	20	V
Out Current	I <sub>O</sub>	100	mA
Power Dissipation	P <sub>D</sub>	150	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ 150	°C

## Electrical Characteristics [Tr1,Tr2:NPN]

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =50V, I <sub>E</sub> =0	-	-	500	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0	-	-	500	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	120	-	-	-
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA	-	0.1	0.3	V
Transition Frequency	f <sub>T</sub> *	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA	-	250	-	MHz
Input Resistance	R <sub>I</sub>	-	-	10	-	KΩ

\* : Characteristic of Transistor Only

Electrical Characteristic Curves

[Tr1,Tr2 :NPN]

Fig. 1  $h_{FE} - I_C$

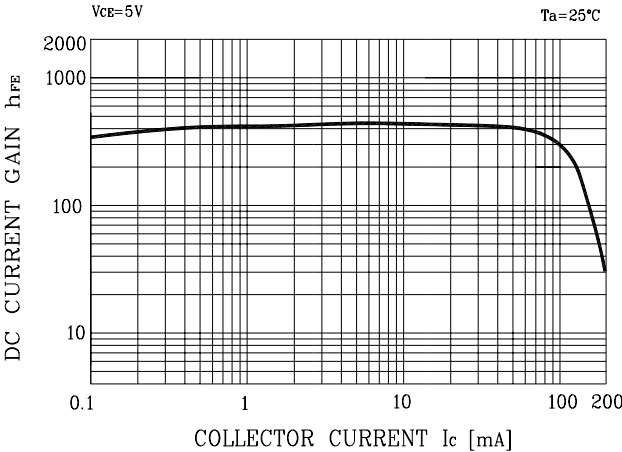


Fig. 2  $V_{CE(SAT)} - I_C$

